



IFW

**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on June 15, 2005.

*Kristi L. Davidson*

Kristi L. Davidson, Reg. No. 44,643

*6/15/05*

Date

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Serial No.: 10/797,425  
Filed: March 10, 2004  
Group Art Unit: 2811  
Examiner: Shouxiang Hu  
Applicant: Pradip K. Roy, Anthony Dip, Allen J. Leith, Seungho Oh  
Title: **SILICON-GERMANIUM THIN LAYER SEMICONDUCTOR  
STRUCTURE WITH VARIABLE SILICON-GERMANIUM  
COMPOSITION AND METHOD OF FABRICATION**  
Attorney Docket: TPS-008  
Confirmation No.: 4397

Cincinnati, Ohio 45202

June 15, 2005

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

In accordance with the duty of candor and good faith imposed by 37 C.F.R. §1.56, and means of complying therewith according to 37 C.F.R. §§1.97 and 1.98, the references listed on the attached Form PTO-1449 are called to the attention of the United States Patent and Trademark Office in connection with the above-identified patent application. Because the requirement (37 C.F.R. §1.98(a)(2)(i)) for submitting copies of U.S. patents and published applications has been

waived, copies of only the foreign cited references and/or other documents are enclosed herewith.

Applicants have also enclosed a copy of the foreign Search Report listing these references.

It is submitted that the cited references do not disclose or render obvious the subject matter claimed in the present application.

**Certifications under 37 C.F.R. § 1.97(e) and § 1.704(d)**

Each item of information contained in the information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement.

Each item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart application and to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 C.F.R. § 1.56(c) more than thirty days prior to the filing of the information disclosure statement.

Applicants do not believe that any fees are due in connection with this submission. However, if such petition is due or any fees are necessary, the Commissioner may consider this to be a request for such and charge any necessary fees to Deposit Account No. 23-3000.

Respectfully submitted,

WOOD, HERRON & EVANS, L.L.P.

By:   
Kristi L. Davidson, Reg. No. 44,643

2700 Carew Tower  
441 Vine Street  
Cincinnati, OH 45202  
(513) 241-2324 (telephone)  
(513) 241-6234 (facsimile)  
K:\TPS\008\Supp IDS.wpd

SUBSTITUTE FORM PTO-1449 (MODIFIED)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. TPS-008		SERIAL NO. 10/797,425	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (Use several sheets if necessary)				APPLICANT Pradip K. Roy et al.			
				FILING DATE March 10, 2004		GROUP 2811	

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER							ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A.A	6	4	2	3	6	3	2	07/23/2002	Samavedam et al.	438	652	07/21/2000
	A.B												
	A.C												
	A.D												
	A.E												
	A.F												
	A.G												
	A.H												
	A.I												
	A.J												
	A.K												

## FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS

		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION (YES/NO)
	A.L						
	A.M						
	A.N						
	A.O						
	A.P						
	A.Q						

## OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)

A.R	Luo et al., <u>Seedless Method of Forming a Silicon Germanium Layer on a Gate Dielectric Layer</u> , US 2004/0009680 A1; publication date 01/15/2004; filed 07/10/2002; U.S. Class 438/933
A.S	Uejima et al., <u>Highly Reliable Poly-SiGe/Amorphous-Si Gate CMOS</u> , Electron Devices Meeting; IEDM Technical Digest; pp. 445-448; 12/10/2000
A.T	

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not in conformance. Draw line through citation only if not in conformance and not considered. Include a copy of this form with next communication to Applicant.